

## Dual N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
20	0.280 at V <sub>GS</sub> = 4.5 V	1.28
	0.360 at V <sub>GS</sub> = 2.5 V	1.13
	0.450 at V <sub>GS</sub> = 1.8 V	1.0

### FEATURES

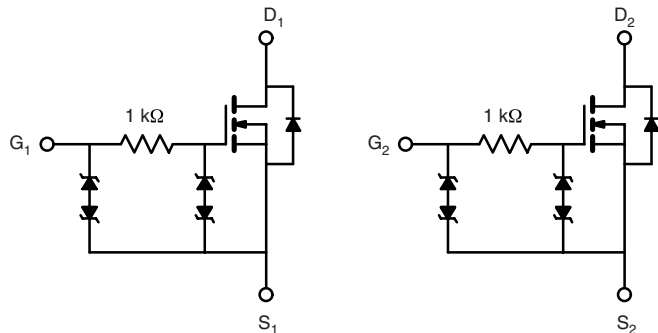
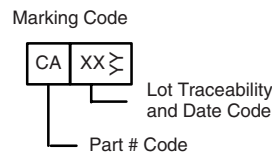
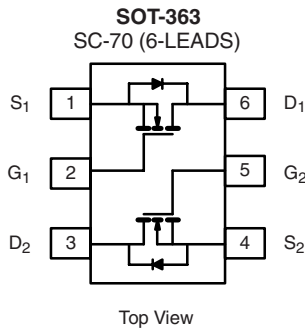
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs: 1.8 V Rated
- ESD Protected: 2000 V
- Thermally Enhanced SC-70 Package
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Load Switching
- PA Switch
- Level Switch



**Ordering Information:** Si1912EDH-T1-E3 (Lead (Pb)-free)  
Si1912EDH-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V <sub>DS</sub>	20		V	
Gate-Source Voltage	V <sub>GS</sub>	± 12			
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	1.28	1.13	A
	T <sub>A</sub> = 85 °C		0.92	0.81	
Pulsed Drain Current	I <sub>DM</sub>	4			
Continuous Diode-Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	0.61	0.48		
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	0.74	0.57	W
	T <sub>A</sub> = 85 °C		0.38	0.30	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 5 s	R <sub>thJA</sub>	130	170	°C/W
	Steady State		170	220	
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	80	100	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

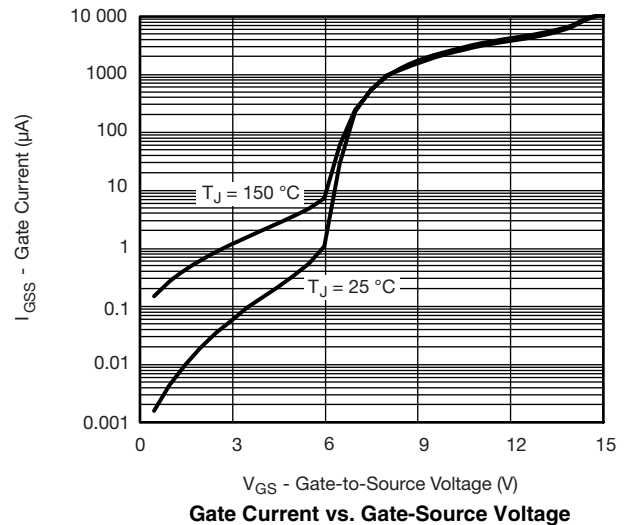
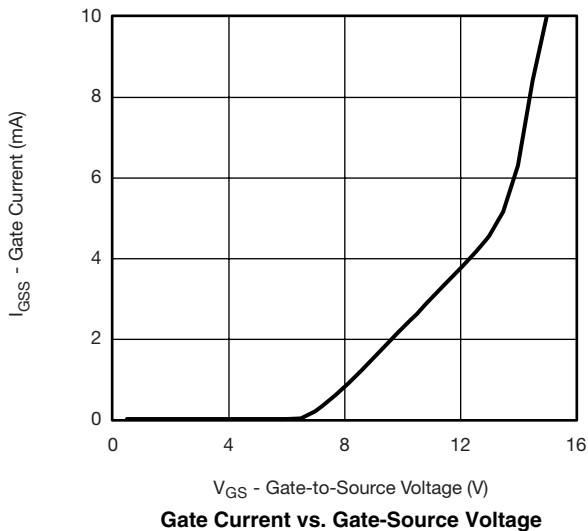
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 100\ \mu\text{A}$	0.45			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 4.5\ \text{V}$			$\pm 1$	$\mu\text{A}$
		$V_{DS} = 0\ \text{V}, V_{GS} = \pm 12\ \text{V}$			$\pm 10$	$\text{mA}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 16\ \text{V}, V_{GS} = 0\ \text{V}$			1	$\mu\text{A}$
		$V_{DS} = 16\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 85\text{ }^\circ\text{C}$			5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5\ \text{V}, V_{GS} = 4.5\ \text{V}$	2			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 4.5\ \text{V}, I_D = 1.13\ \text{A}$		0.220	0.280	$\Omega$
		$V_{GS} = 2.5\ \text{V}, I_D = 0.99\ \text{A}$		0.281	0.360	
		$V_{GS} = 1.8\ \text{V}, I_D = 0.2\ \text{A}$		0.344	0.450	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 10\ \text{V}, I_D = 1.13\ \text{A}$		2.6		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 0.48\ \text{A}, V_{GS} = 0\ \text{V}$		0.8	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 10\ \text{V}, V_{GS} = 4.5\ \text{V}, I_D = 1.13\ \text{A}$		0.65	1	nC
Gate-Source Charge	$Q_{gs}$			0.2		
Gate-Drain Charge	$Q_{gd}$			0.23		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\ \text{V}, R_L = 20\ \Omega$ $I_D \cong 0.5\ \text{A}, V_{GEN} = 4.5\ \text{V}, R_g = 6\ \Omega$		45	70	ns
Rise Time	$t_r$			85	130	
Turn-Off Delay Time	$t_{d(off)}$			350	530	
Fall Time	$t_f$			210	320	

**Notes**

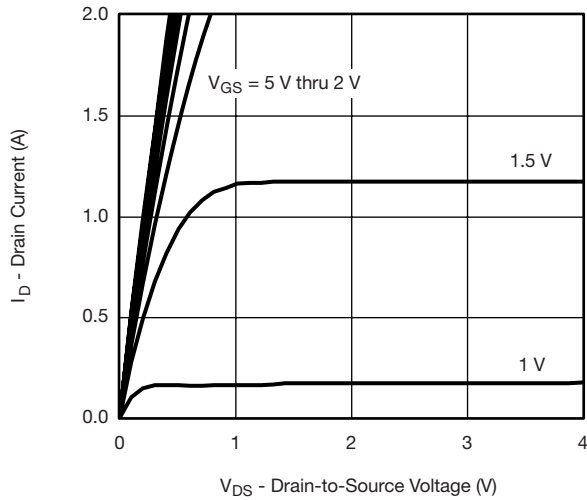
- a. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

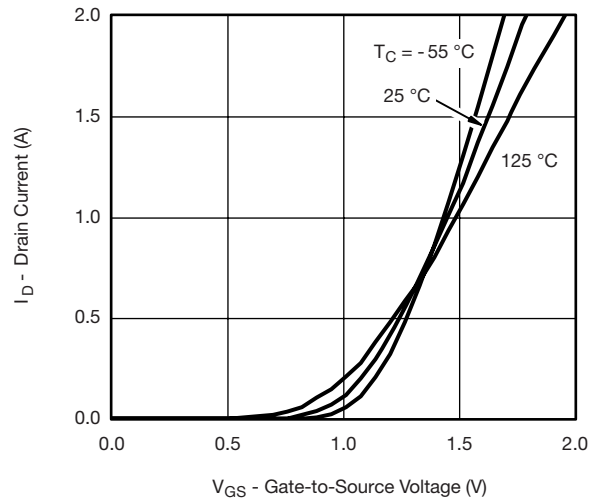
**TYPICAL CHARACTERISTICS**  $25\text{ }^\circ\text{C}$ , unless otherwise noted



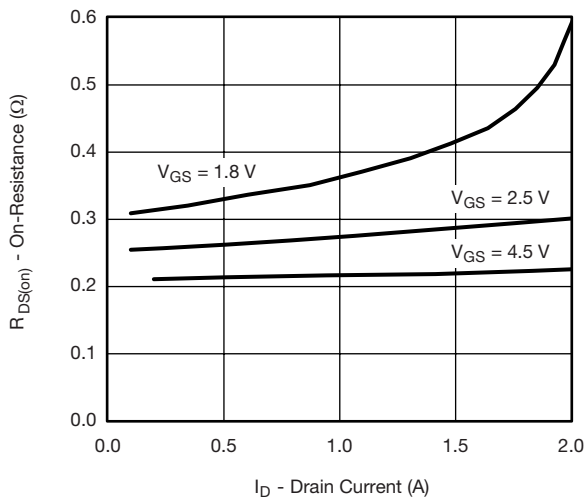
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



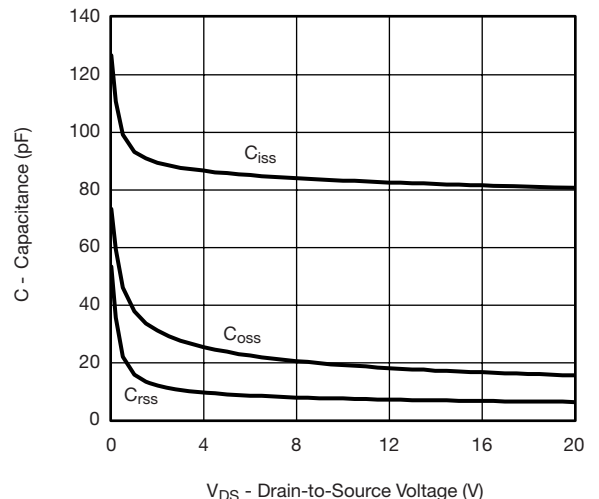
**Output Characteristics**



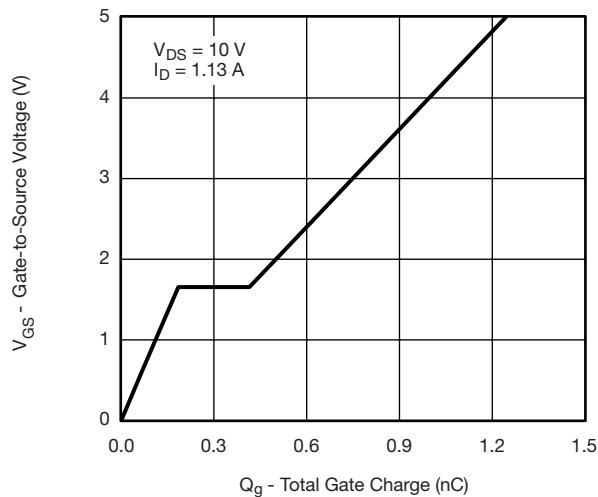
**Transfer Characteristics**



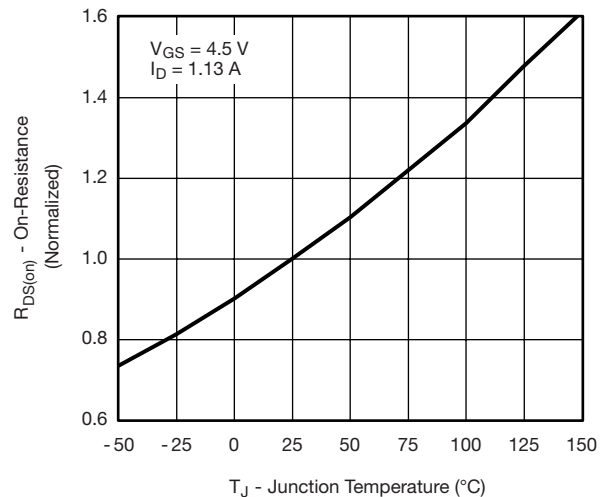
**On-Resistance vs. Drain Current**



**Capacitance**

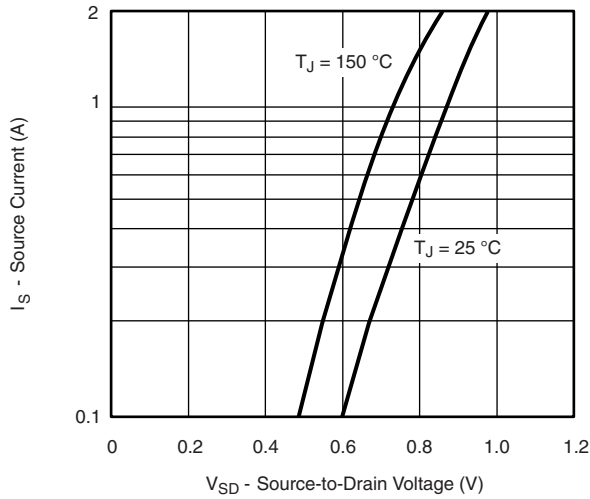


**Gate Charge**

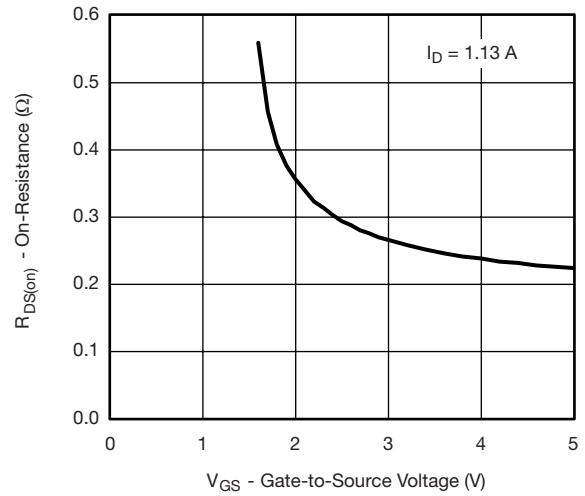


**On-Resistance vs. Junction Temperature**

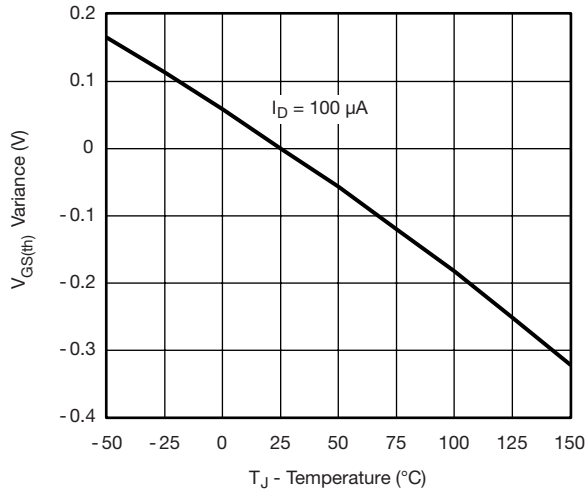
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



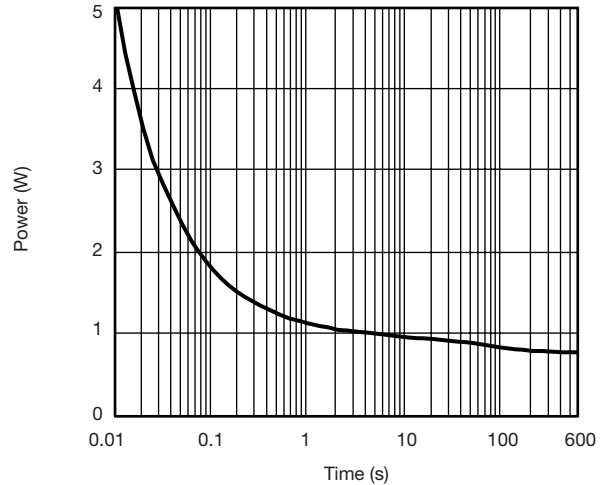
**Source-Drain Diode Forward Voltage**



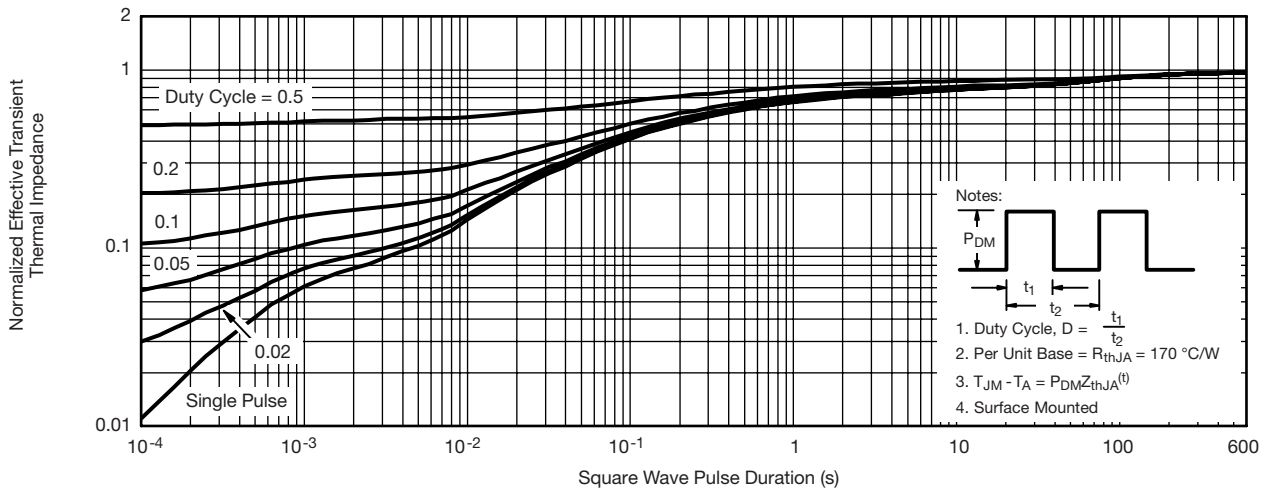
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**

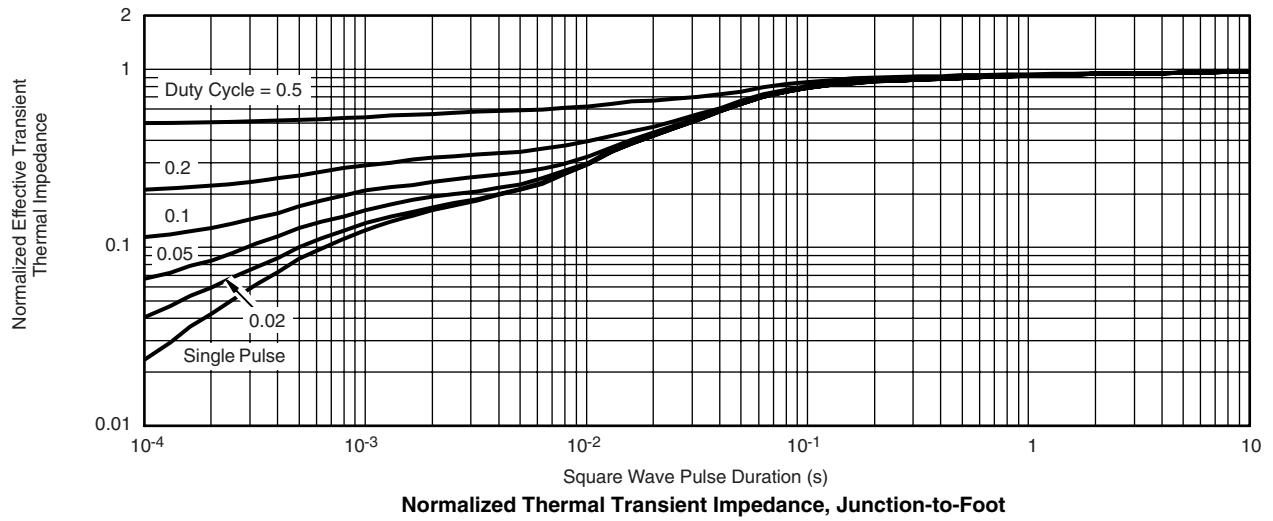


**Single Pulse Power, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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